

General Description

The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS® Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity





Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

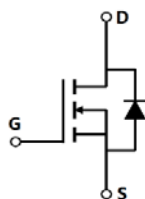
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	650	V
$I_D, pulse$	60	A
$R_{DS(ON), max} @ V_{GS}=10V$	180	mΩ
Q_g	23.3	nC

Marking Information

Product Name	Package	Marking
OSG60R180HF	TO247	OSG60R180H

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	20	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		12.5	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	60	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	20	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	60	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	151	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	600	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.82	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$
		650				$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2		4	V	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.15	0.18	Ω	$V_{GS}=10\text{ V}$, $I_D=10\text{ A}$
			0.38			$V_{GS}=10\text{ V}$, $I_D=10\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1440		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		105		pF	
Reverse transfer capacitance	C_{rss}		3.94		pF	
Turn-on delay time	$t_{d(on)}$		40.3		ns	$V_{GS}=10\text{ V}$, $V_{DS}=480\text{ V}$, $R_G=25\ \Omega$, $I_D=20\text{ A}$
Rise time	t_r		49.3		ns	
Turn-off delay time	$t_{d(off)}$		60		ns	
Fall time	t_f		59.2		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		23.3		nC	$V_{GS}=10\text{ V}$, $V_{DS}=480\text{ V}$, $I_D=20\text{ A}$
Gate-source charge	Q_{gs}		6.6		nC	
Gate-drain charge	Q_{gd}		8.3		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		367.2		ns	$V_R=400\text{ V}$, $I_S=20\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		4.2		μC	
Peak reverse recovery current	I_{rrm}		24.3		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=150\text{ V}$, $V_{GS}=10\text{ V}$, $L=10.8\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

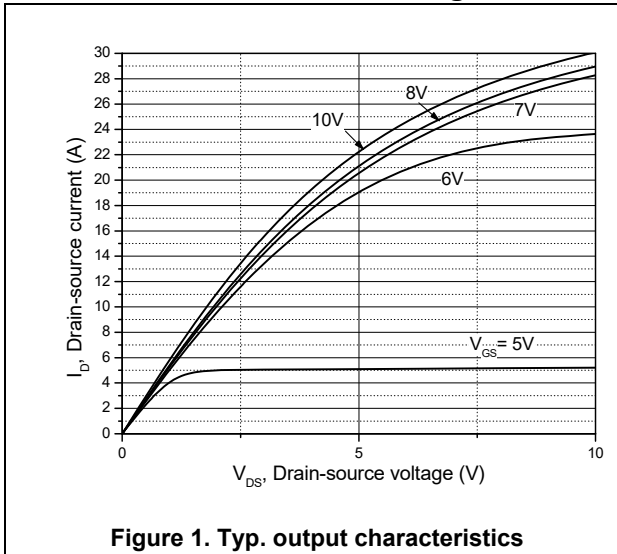


Figure 1. Typ. output characteristics

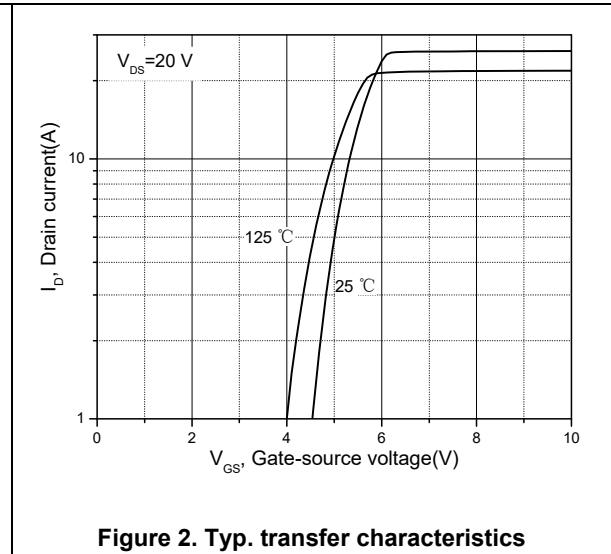


Figure 2. Typ. transfer characteristics

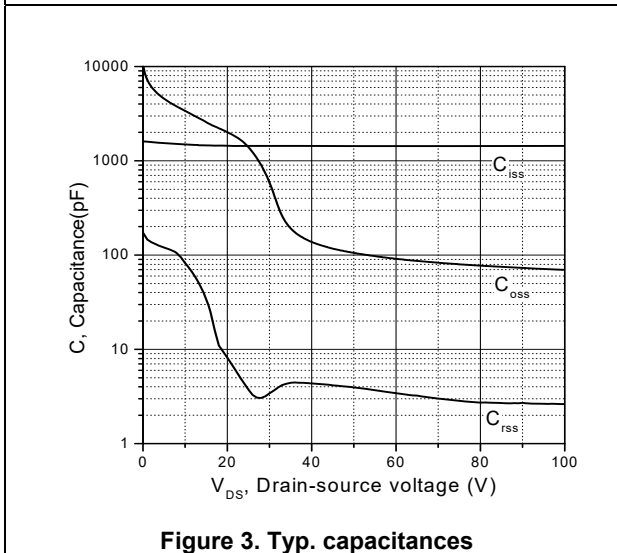


Figure 3. Typ. capacitances

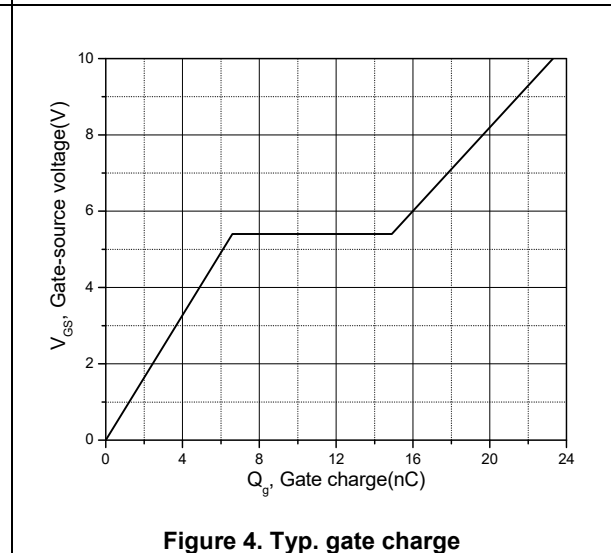


Figure 4. Typ. gate charge

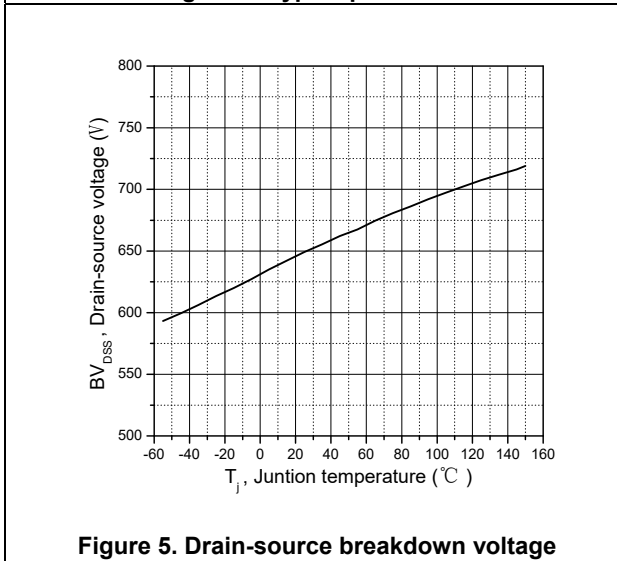


Figure 5. Drain-source breakdown voltage

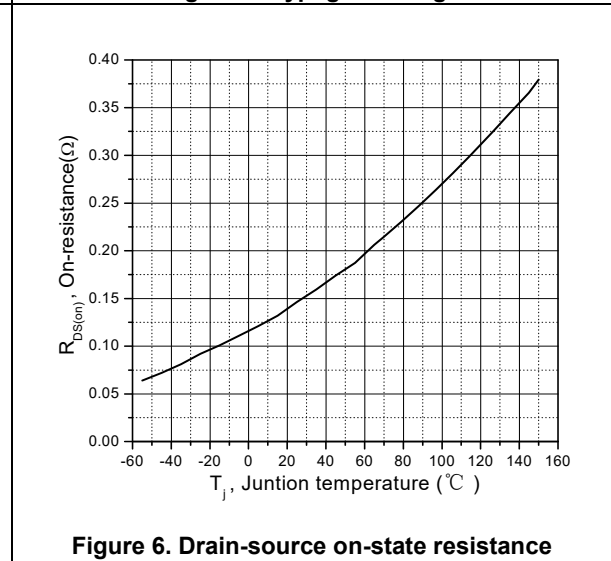


Figure 6. Drain-source on-state resistance

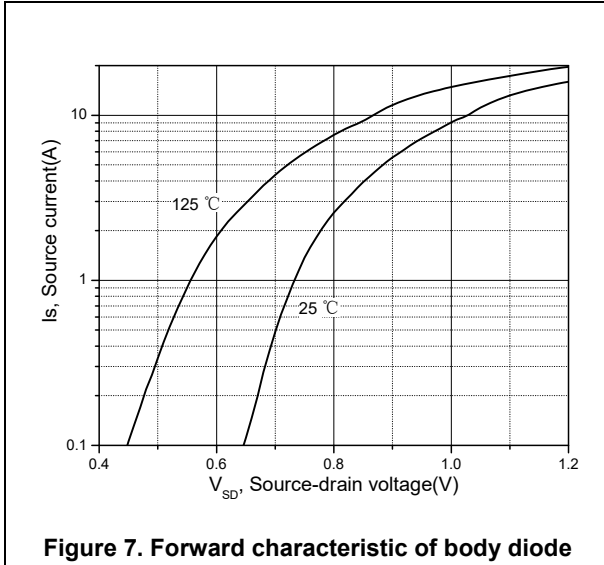


Figure 7. Forward characteristic of body diode

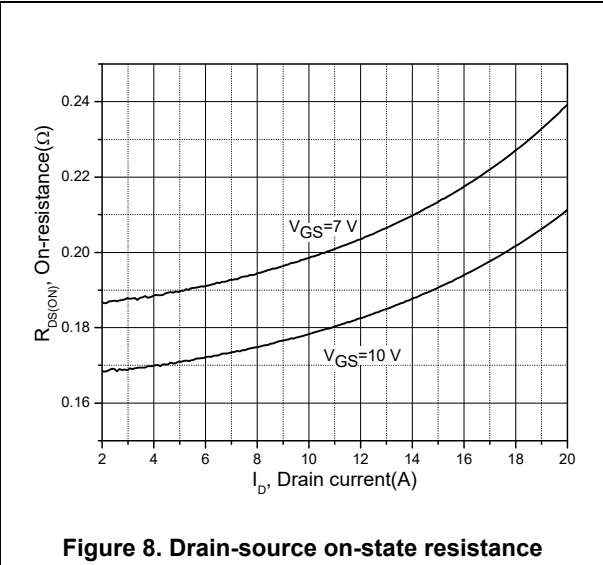


Figure 8. Drain-source on-state resistance

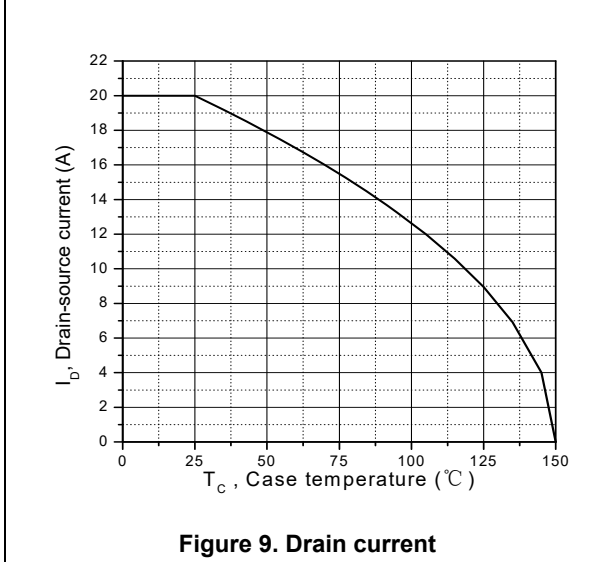


Figure 9. Drain current

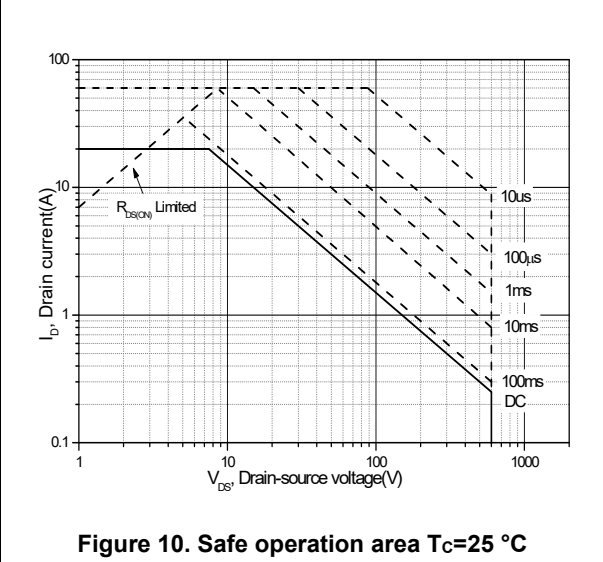


Figure 10. Safe operation area Tc=25 °C

Test circuits and waveforms

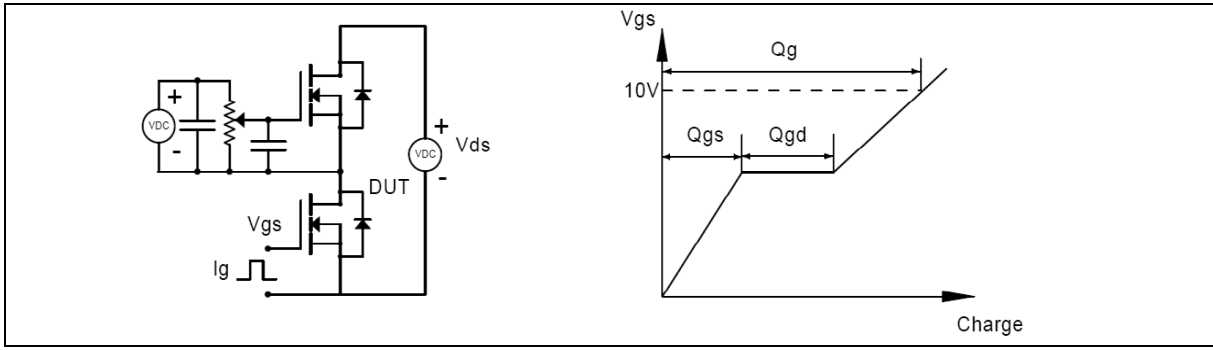


Figure 1. Gate charge test circuit & waveform

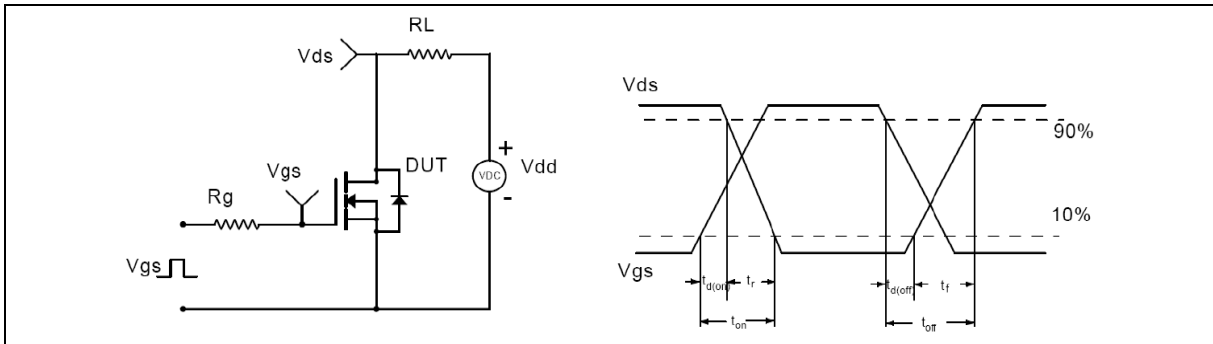


Figure 2. Switching time test circuit & waveforms

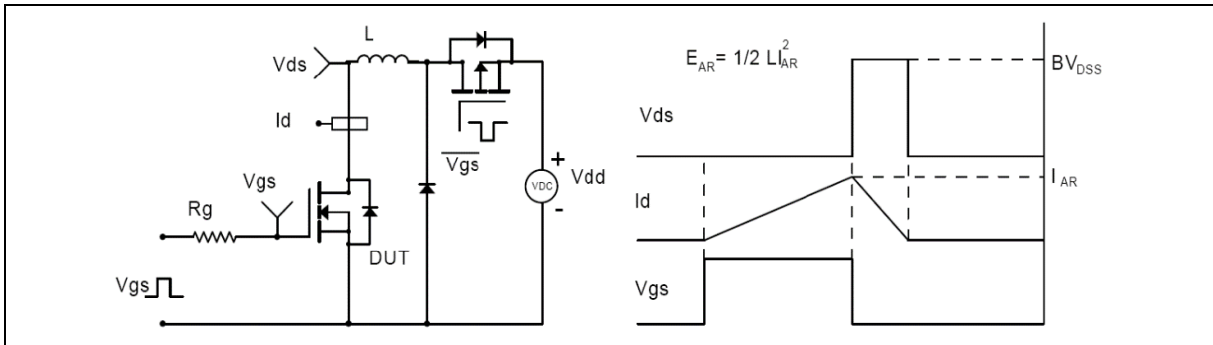


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

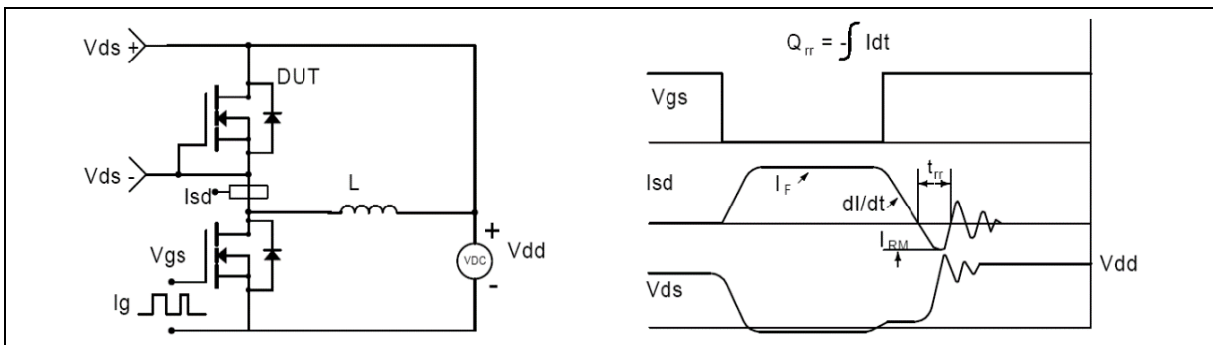
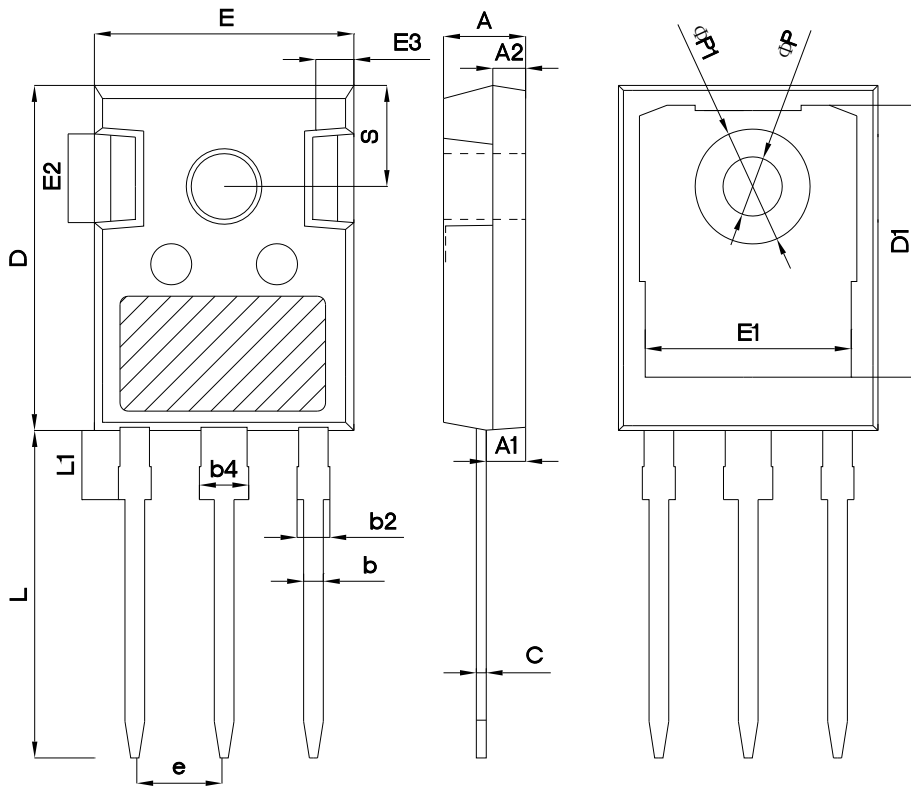


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15 BSC		

Version 1.; TO247-P outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-P	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R180HF	TO247	yes	yes	yes

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